# **Dual 4-Bit Binary Ripple Counter**

The MC74VHC393 is an advanced high speed CMOS dual 4-bit binary ripple counter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This device consists of two independent 4-bit binary ripple counters with parallel outputs from each counter stage. A  $\div 256$  counter can be obtained by cascading the two binary counters.

Internal flip—flops are triggered by high—to—low transitions of the clock input. Reset for the counters is asynchronous and active—high. State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used as clocks or as strobes except when gated with the Clock of the VHC393.

The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed:  $f_{max} = 170 \text{ MHz}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 4 \mu A$  (Max) at  $T_A = 25^{\circ}C$
- High Noise Immunity:  $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: V<sub>OLP</sub> = 0.8 V (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 236 FETs or 59 Equivalent Gates



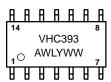
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#### MARKING DIAGRAMS

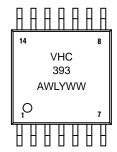


SOIC-14 D SUFFIX CASE 751A

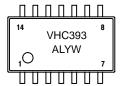




TSSOP-14 DT SUFFIX CASE 948G







A = Assembly Location

L, WL = Wafer Lot Y = Year W, WW = Work Week

#### ORDERING INFORMATION

Device	Package	Shipping
MC74VHC393D	SOIC-14	55 Units/Rail
MC74VHC393DT	TSSOP-14	96 Units/Rail
MC74VHC393DTR2	TSSOP-14	2500 Units/Reel
MC74VHC393M	SOIC EIAJ-14	50 Units/Rail
MC74VHC393MEL	SOIC EIAJ-14	2000 Units/Reel

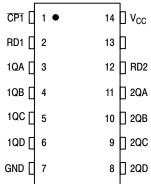


Figure 1. Pin Assignment

3, 11 nQA **BINARY** 4, 10 nQB COUNTER <u>CPn</u> \_\_1, 13 5, 9 nQC 6, 8 nQD

Figure 2. Logic Diagram

2, 12

RDn

#### **FUNCTION TABLE**

Inp	uts	
Clock	Outputs	
Χ	Н	L
Н	L	No Change
L	L	No Change
<b>↑</b>	L	No Change
$\rightarrow$	L	Next State

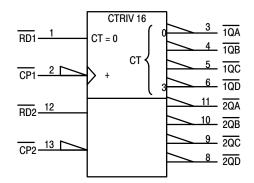


Figure 3. IEC Logic Symbol

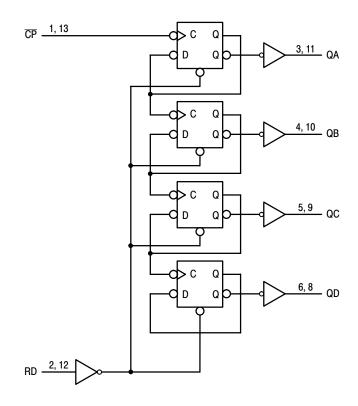


Figure 4. Expanded Logic Diagram

#### **MAXIMUM RATINGS\***

Symbol	Parameter	r	Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to + 7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to + 7.0	V
V <sub>OUT</sub>	DC Output Voltage		$-0.5$ to $V_{CC}$ + 0.5	V
I <sub>IK</sub>	Input Diode Current		-20	mA
I <sub>OK</sub>	Output Diode Current		±20	mA
I <sub>OUT</sub>	DC Output Current, per Pin		±25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GI	ND Pins	±75	mA
P <sub>D</sub>	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T <sub>stg</sub>	Storage Temperature		-65 to + 150	°C

<sup>\*</sup> Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range GND  $\leq$  ( $V_{in}$  or  $V_{out}$ )  $\leq$   $V_{CC}$ .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	DC Supply Voltage	2.0	5.5	V
V <sub>IN</sub>	DC Input Voltage	0	5.5	V
V <sub>OUT</sub>	DC Output Voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Operating Temperature	-55	+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time $ V_{CC} = 3.3 \text{ V} $ $ V_{CC} = 5.0 \text{ V} $	0 0	100 20	ns/V

The  $\theta_{JA}$  of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

## DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

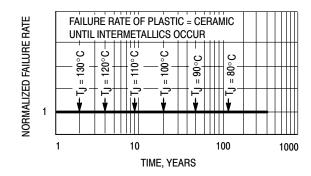


Figure 5. Failure Rate vs. Time Junction Temperature

<sup>†</sup>Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C TSSOP Package: – 6.1 mW/°C from 65° to 125°C

#### DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	Т	A = 25°	°C	T <sub>A</sub> = 5	≤ 85°C	<b>T</b> <sub>A</sub> = ≤	125°C	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85			1.5 2.1 3.15 3.85		1.5 2.1 3.15 3.85		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		2.0 3.0 4.5 5.5			0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65		0.5 0.9 1.35 1.65	V
V <sub>OH</sub>	Minimum High-Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50  \mu\text{A}$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low–Level Output Voltage V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub>	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OL} = 50 \mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> I <sub>OL</sub> = 4 mA I <sub>OL</sub> = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	1
I <sub>IN</sub>	Maximum Input Leakage Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		±1.0	μΑ
Icc	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ

#### AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns)

			T <sub>A</sub> = 25°C		T <sub>A</sub> = 5	≤ 85°C		= ≤ 5°C		
Symbol	Parameter	<b>Test Conditions</b>	Min	Тур	Max	Min	Max	Min	Max	Unit
f <sub>max</sub>	Maximum Clock Frequency (50% Duty Cycle)	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		120 65		65 35		65 35		MHz
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		170 115		105 75		105 75		=
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CP to QA	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		8.6 11.1	13.2 16.7	1.0 1.0	15.5 19.0	1.0 1.0	15.5 19.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		5.8 7.3	8.5 10.5	1.0 1.0	10.0 12.0	1.0 1.0	10.0 12.0	=
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CP to QB	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		10.2 12.7	15.8 19.3	1.0 1.0	18.5 22.0	1.0 1.0	18.5 22.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		6.8 8.3	9.8 11.8	1.0 1.0	11.5 13.5	1.0 1.0	11.5 13.5	=
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CP to QC	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		11.7 14.2	18.0 21.5	1.0 1.0	21.0 24.5	1.0 1.0	21.0 24.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		7.7 9.2	11.2 13.2	1.0 1.0	13.0 15.0	1.0 1.0	13.0 15.0	=
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, CP to QD	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		13.0 15.5	19.7 23.2	1.0 1.0	23.0 26.5	1.0 1.0	23.0 26.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		8.5 10.0	12.5 14.5	1.0 1.0	14.5 16.5	1.0 1.0	14.5 16.5	
t <sub>PHL</sub>	Maximum Propagation Delay, RD to QN	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		7.9 10.4	12.3 15.8	1.0 1.0	14.5 18.0	1.0 1.0	14.5 18.0	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ p}$ $C_L = 50 \text{ p}$		5.4 6.9	8.1 10.1	1.0 1.0	9.5 11.5	1.0 1.0	9.5 11.5	ns

#### AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ns}$ )

			T <sub>A</sub> = 25°C		<b>T</b> <sub>A</sub> = ≤	≤ 85°C	T <sub>A</sub> 125	= ≤ 5°C		
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>OSLH</sub> , t <sub>OSHL</sub>	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 1)			1.5		1.5		1.5	pF
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 1)			1.0		1.0		1.0	pF
C <sub>IN</sub>	Maximum Input Capacitance			4.0	10		10		10	pF

		Typical @ 25°C, V <sub>CC</sub> = 5.0V	
$C_PD$	Power Dissipation Capacitance (Note 2)	23	pF

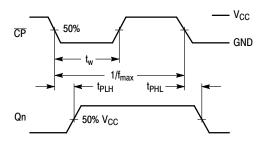
#### **NOISE CHARACTERISTICS** (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T <sub>A</sub> = 25°C		
Symbol	Parameter	Тур	Max	Unit
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	0.5	0.8	V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	-0.5	-0.8	V
V <sub>IHD</sub>	Minimum High Level Dynamic Input Voltage		3.5	V
$V_{ILD}$	Maximum Low Level Dynamic Input Voltage		1.5	V

#### **TIMING REQUIREMENTS** (Input $t_r = t_f = 3.0 \text{ns}$ )

			TA	= 25°C	T <sub>A</sub> = ≤ 85°C	<b>T</b> <sub>A</sub> = ≤ 125°C	
Symbol	Parameter	Test Conditions	Тур	Limit	Limit	Limit	Unit
t <sub>w</sub>	Minimum Pulse Width, CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 5.0	5.0 5.0	5.0 5.0	ns
t <sub>w</sub>	Minimum Pulse Width, RD	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 5.0	5.0 5.0	5.0 5.0	ns
t <sub>rec</sub>	Minimum Recovery Time, RD to CP	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		5.0 4.0	5.0 4.0	5.0 4.0	ns
t <sub>r</sub> , t <sub>f</sub>	Minimum Input Rise and Fall Times	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \pm 0.5 \text{ V}$		330 100	330 100	330 100	ns

Parameter guaranteed by design. t<sub>OSLH</sub> = |t<sub>PLHm</sub> - t<sub>PLHn</sub>|, t<sub>OSHL</sub> = |t<sub>PHLm</sub> - t<sub>PHLn</sub>|.
 C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: |c<sub>C(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no-load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.



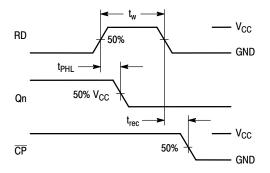
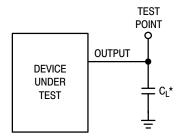


Figure 6. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 7. Test Circuit

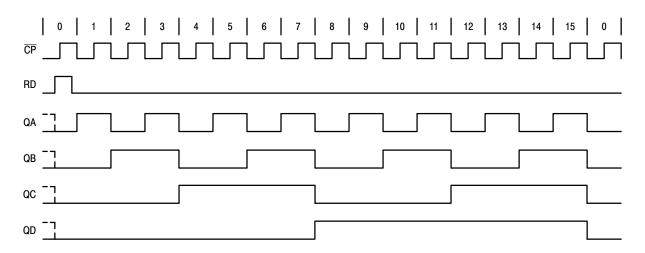


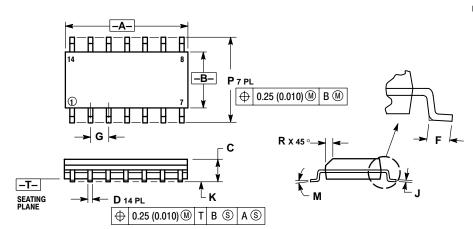
Figure 8. Timing Diagram

#### **COUNT SEQUENCE**

	Outputs							
Count	QD	QC	QB	QA				
0	L	L	L	L				
1	L	L	L	Н				
2	L	L	Н	L				
3	L	L	Н	Н				
4	L	Н	L	L				
5	L	Н	L	Н				
6	L	Н	Н	L				
7	L	Н	Н	Н				
8	Н	L	L	L				
9	Н	L	L	Н				
10	Н	L	Н	L				
11	Н	L	Н	Н				
12	Н	Н	L	L				
13	Н	Н	L	Н				
14	Н	Н	Н	L				
15	Н	Η	I	Н				

#### **PACKAGE DIMENSIONS**

#### **D SUFFIX** SOIC-14 CASE 751A-03 **ISSUE F**

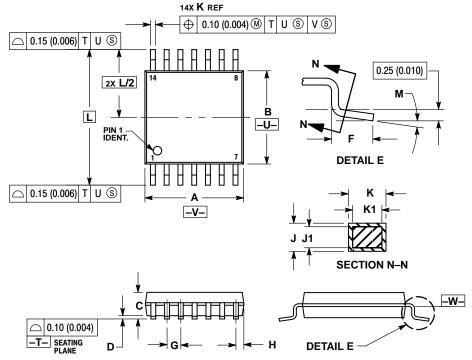


- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	8.55	8.75	0.337	0.344	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27 BSC		0.050 BSC		
7	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
M	0°	7°	0°	7°	
Р	5.80	6.20	0.228	0.244	
R	0.25	0.50	0.010	0.019	

#### **PACKAGE DIMENSIONS**

#### **DT SUFFIX TSSOP** CASE 948G-01 **ISSUE 0**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: MILLIMETER.
  3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
  4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.019) PER SIDE.
  5. DIMENSION K DOES NOT INCLUDE DAMBAR
- 0.25 (0.010) PER SIDE.

  5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

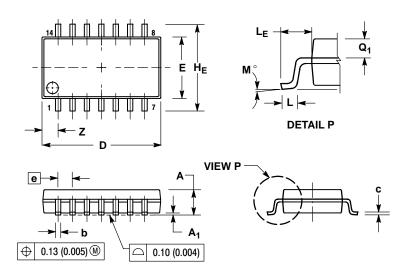
  6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

  7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W-.

	MILLIN	IETEDO	INCHES	
	MILLIMETERS			
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

#### **PACKAGE DIMENSIONS**

#### **M SUFFIX** SO-14 **CASE 965-01 ISSUE 0**



#### NOTES:

- NOTES:

  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

  2. CONTROLLING DIMENSION: MILLIMETER.

  3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) DED SIDE
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
  PER SIDE.
  1 TERMINAL NUMBERS ARE SHOWN FOR
  REFERENCE ONLY.
  5. THE LEAD WIDTH DIMENSION (b) DOES NOT
  INCLUDE DAMBAR PROTRUSION. ALLOWABLE
  DAMBAR PROTRUSION SHALL BE 0.08 (0.003)
  TOTAL IN EXCESS OF THE LEAD WIDTH
  DIMENSION AT MAXIMUM MATERIAL CONDITION.
  DAMBAR CANNOT BE LOCATED ON THE LOWER
  RADIUS OR THE FOOT. MINIMUM SPACE
  BETWEEN PROTRUSIONS AND ADJACENT LEAD
  TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A <sub>1</sub>	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
Е	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10 °	0 °	10 °
$Q_1$	0.70	0.90	0.028	0.035
Z		1.42		0.056

## **Notes**

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